2SK4208

Silicon N-channel enhancement MOS FET

For high speed switching circuits

■ Features

- \bullet Gate-source surrender voltage V_{GSS} : $\pm 30~V$ guaranteed
- Avalanche energy capability guaranteed: EAS > 801 mJ
- High-speed switching: $t_f = 88 \text{ ns (typ.)}$

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	$V_{ m DSS}$	200	V	
Gate-source surrender voltage	V _{GSS}	±30	V	
Drain current	I_D	±30	A	
Peak drain current *	I_{DP}	±160	A	
Avalanche energy capability	EAS	801	mJ	
Avalanche energy capability *	EAR	224	mJ	
Drain power dissipation $T_a = 25^{\circ}C$	P_{D}	40	W	
		2.0	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: Assurance of repetitive pulse. (Repetitive period $\leq 5 \,\mu s$ on-duty $\leq 20\%$)

But, it must stay within 40% of all that the time impressed pulse repetitively.

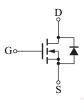


■ Package

- Code
- TO-220D-A1
- Pin Name
 - 1: Gate
 - 2: Drain
 - 3: Source

■ Marking Symbol: K4208

■ Internal Connection



■ Electrical Characteristics $T_C = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	200			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 160 \text{ V}, V_{GS} = 0$			1.0	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			±1.0	μΑ
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1.0 \text{ mA}$	2.5		4.5	V
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 15.0 \text{ A}$		43	52	mΩ
Forward transfer conductance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 15.0 \text{ A}$	12	22		S
Short-circuit input capacitance (Common source)	C _{iss}			1970		pF
Short-circuit output capacitance (Common source)	C _{oss}	$V_{DS} = 2.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		400		pF
Reverse transfer capacitance (Common source)	C _{rss}			85		pF
Turn-on delay time	t _{d(on)}			32		ns
Rise time	t _r	$V_{DD} = 100 \text{ V}, I_D = 15.0 \text{ A}$		130		ns
Turn-off delay time	t _{d(off)}	$R_L \approx 6.7 \Omega$, $V_{GS} = 10 V$		170		ns
Fall time	$t_{\rm f}$			88		ns

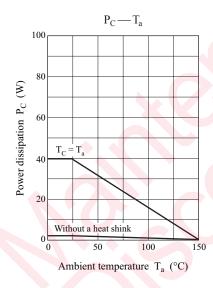
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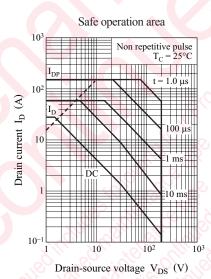
Panasonic

■ Electrical Characteristics (continued) $T_C = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode forward voltage	V _{DSF}	$I_{DR} = 30 \text{ A}, V_{GS} = 0$			-1.5	V
Reverse recovery time	t _{rr}	$L = 230 \mu H, V_{DD} = 100 V$		220		ns
Reverse recovery charge	Q _{rr}	$I_{DR} = 13.0 \text{ A}, d_i / d_t = 100 \text{ A/}\mu\text{s}$		1.1		nC
Gate charge load	Qg			66		nC
Gate-source charge	Q _{gs}	$V_{DD} = 100 \text{ V}, I_D = 15.0 \text{ A}, V_{GS} = 10 \text{ V}$		11		nC
Gate-drain charge	Q _{gd}			34		nC
Thermal resistance (ch-c)	R _{th(ch-c)}				3.13	°C/W
Thermal resistance (ch-a)	R _{th(j-a)}				62.5	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

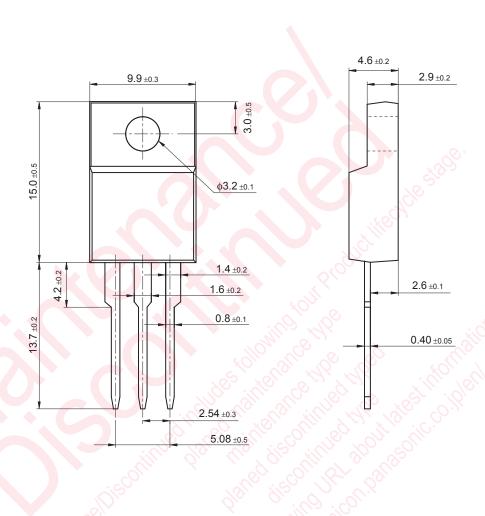




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TO-220D-A1

Unit: mm



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